

# Contents

<b>List of contributors</b>	<b>xi</b>
<b>Woodhead Publishing Series in Electronic and Optical Materials</b>	<b>xiii</b>
<b>Part One Semiconductor materials for nanowires</b>	<b>1</b>
<b>1 II–VI semiconductor nanowires: ZnO</b>	<b>3</b>
<i>J. Miao, B. Liu</i>	
1.1 Introduction	3
1.2 Physical properties of ZnO	5
1.3 Methods for the preparation of 1D ZnO nanostructures	8
1.4 Applications of 1D ZnO nanostructures	14
1.5 Conclusion	24
References	25
<b>2 II–VI compound semiconductor nanowires: Optical properties and nanophotonics</b>	<b>29</b>
<i>H. Yu, C. Xin, Q. Zhang, M.I.B. Utama, L. Tong, Q.H. Xiong</i>	
2.1 Introduction	29
2.2 II–VI semiconductor nanowires synthesis	30
2.3 Steady-state photoluminescence spectroscopy	36
2.4 Time-resolved photoluminescence spectroscopy	41
2.5 Nanowire waveguides and functional devices	47
2.6 Nanowire photoluminescence and lasers	54
2.7 Conclusions and outlook	59
References	59
<b>3 Advanced III–V nanowire growth toward large-scale integration</b>	<b>71</b>
<i>X. Dai, A. Olivier, C. Wilhelm, S.A. Dayeh, C. Soci</i>	
3.1 Synthesis of III–V NWs	71
3.2 Crystallographic properties	82
3.3 Applications of III–V nanowires	93
3.4 Conclusion	106
References	106

<b>4</b>	<b>III–V semiconductor nanowires: nitrides (N-based; III-N)</b>	<b>125</b>
	<i>P. Dogan, C. Chèze, R. Calarco</i>	
4.1	Introduction: the importance of III-nitride alloys	125
4.2	III-nitride nanowires: brief historical overview	126
4.3	GaN nanowires	127
4.4	(In,Ga)N alloy and heterostructure nanowires	133
4.5	(Al,Ga)N alloy and heterostructure nanowires	134
4.6	Conclusions	136
	References	136
 <b>Part Two Characterizing the properties of semiconductor nanowires</b>		 <b>147</b>
<b>5</b>	<b>Self-assembly and organization of nanowires</b>	<b>149</b>
	<i>Lele Peng, Ye Shi, Guihua Yu</i>	
5.1	Introduction	149
5.2	Langmuir–Blodgett technique	150
5.3	Optical trapping method	153
5.4	Contact printing method	156
5.5	Electric field-assisted assembly	156
5.6	Magnetic field-assisted assembly	158
5.7	Microfluidic assembly	161
5.8	Chemically driven assembly	163
5.9	Blown bubble film method	166
5.10	Conclusions and perspectives	169
	References	170
<b>6</b>	<b>Quantum transport in semiconductor nanowires</b>	<b>173</b>
	<i>M. Bescond</i>	
6.1	Introduction	173
6.2	Theory and modeling	174
6.3	Interface-induced correlation effects	180
6.4	Transport through single ionized impurities	186
6.5	Impact of phonon scattering	194
	References	200
<b>7</b>	<b>Measuring the properties of semiconductor nanowires with transmission electron microscopy</b>	<b>203</b>
	<i>K.A. Dick</i>	
7.1	Sample preparation	203
7.2	Structural properties	204
7.3	Morphology	207
7.4	Compositional analysis	208
7.5	<i>In situ</i> analysis of properties	212

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7.6	Summary and outlook	215
	References	216
<b>8</b>	<b>Electron holography of nanowires – Part 1</b>	<b>221</b>
	<i>Luying Li</i>	
8.1	Application details	221
8.2	Sources of future information and advice	247
	Acknowledgements	247
	References	247
<b>9</b>	<b>Electron holography of nanowires – Part 2</b>	<b>253</b>
	<i>Martien Ilse den Hertog</i>	
9.1	Introduction to electron holography	253
9.2	Challenges with 2D samples	261
9.3	Nanowire sample preparation	262
9.4	Literature on nanowires	263
9.5	Off-axis holography of semiconducting NWs	263
9.6	Conclusion and perspectives	272
9.7	Further reading	273
	Acknowledgements	273
	References	273
<b>10</b>	<b>Electrical characterization of semiconductor nanowires by scanning-probe microscopy</b>	<b>277</b>
	<i>T. Xu, B. Grandier</i>	
10.1	Introduction	277
10.2	Instrumentation	278
10.3	Exploring the surfaces of semiconductor nanowires at the nanoscale	285
10.4	Studying transport in semiconductor nanowires	292
10.5	Conclusion	297
	References	298
<b>11</b>	<b>Using atom probe tomography in the study of semiconductor nanowires</b>	<b>305</b>
	<i>W. Chen, P. Pareige</i>	
11.1	Introduction	305
11.2	Instrumentation	305
11.3	Basic principle of APT	307
11.4	Nanowire sample preparations for atom probe	311
11.5	Characterization of SiNWs	317
11.6	Summary and perspectives	324
	Acknowledgements	324
	References	325

<b>12</b>	<b>Optoelectronic properties of semiconductor nanowires</b>	<b>327</b>
	<i>A. Pan, X. Zhu</i>	
12.1	Introduction	327
12.2	The characterization of photoelectric properties	328
12.3	The optoelectronic properties of the NWs	332
12.4	Conclusions	357
	References	357
<b>13</b>	<b>Semiconductor nanowires studied by photocurrent spectroscopy</b>	<b>365</b>
	<i>N. Erhard, A. Holleitner</i>	
13.1	Introduction	365
13.2	Methods	366
13.3	Photocurrent dynamics in semiconductor nanowires	369
13.4	Absorption effects in semiconductor nanowires	374
13.5	Morphologies explored by photocurrent spectroscopy	376
13.6	Conclusion and future trends	381
13.7	Sources for further information	382
	Acknowledgements	382
	References	382
<b>14</b>	<b>Cathodoluminescence microanalysis of ZnO nanowires</b>	<b>393</b>
	<i>C. Ton-That, M.R. Phillips</i>	
14.1	Review of the cathodoluminescence technique	393
14.2	Brief overview of luminescence centres in ZnO	395
14.3	STEM cathodoluminescence	404
14.4	Conclusions	405
	Acknowledgements	406
	References	406
<b>Part Three</b>	<b>Applications of semiconductor nanowires</b>	<b>409</b>
<b>15</b>	<b>Semiconductor nanowires for solar cells</b>	<b>411</b>
	<i>P. Thony</i>	
15.1	Introduction: photovoltaic conversion for renewable energy	411
15.2	Solar cell devices and technologies	412
15.3	Nanowire concept in photovoltaic solar cells	418
15.4	Nanowire fabrication for photovoltaic devices	424
15.5	Achievements and perspectives	432
	References	433
<b>16</b>	<b>Semiconductor nanowire battery electrodes</b>	<b>441</b>
	<i>L.Q. Mai</i>	
16.1	Introduction	441
16.2	Properties of nanowires for energy storage	442

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16.3	<i>In situ</i> probing on single nanowire	443
16.4	Nanowire structure	447
16.5	Conclusions	462
	Acknowledgements	462
	References	463
<b>17</b>	<b>Semiconductor nanowires for biosensors</b>	<b>471</b>
	<i>Anqi Zhang, Gengfeng Zheng</i>	
17.1	Introduction	471
17.2	Fundamental principle for FET sensors	472
17.3	Examples of semiconductor nanowire FET sensors	474
17.4	Methods for enhancing the sensitivity of semiconductor nanowire sensors	479
17.5	Conclusion	486
17.6	Future trends	486
	Acknowledgements	487
	References	487
<b>18</b>	<b>Hybrid semiconductor/plasmonic nanowires for nanoscale photonic devices</b>	<b>491</b>
	<i>Li Zhou, Q. Zhang, Qu-Quan Wang</i>	
18.1	Introduction	491
18.2	Plasmonic nanowire waveguide and plasmon–exciton interaction in plasmonic nanowires	491
18.3	Coupling between semiconductor nanowires and surface plasmons	505
18.4	Summary	515
	References	516
<b>19</b>	<b>Electrical interfacing of nanowire devices with cells and tissues</b>	<b>521</b>
	<i>M. Paul, G. Murray, B. Tian</i>	
19.1	Introduction: interfacing to cellular systems	521
19.2	Signal transduction mechanism: field-effect transistor-based detection	525
19.3	Nanowire sensors for extracellular electrical recording	526
19.4	Nanowire sensors for intracellular electrical recordings	531
19.5	Future trends	537
	References	538
	<b>Index</b>	<b>543</b>